

ABSTRACT

There is provided a technology for obtaining an electrode having a low
5 contact resistance and less surface roughness. There is provided an
electrode comprising a semiconductor film 101, and a first metal layer 102
and a second metal layer 103 sequentially stacked in this order on the
semiconductor film 101, characterized in that the first metal film 102 is
formed of Al, and the second metal film 103 is formed of at least one metal
10 selected from the group consisting of Nb, W, Fe, Hf, Re, Ta and Zr.